# 2SC5557

### Silicon NPN epitaxial planar type

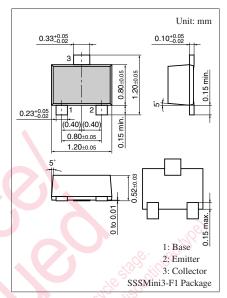
For low-noise RF amplifier

#### ■ Features

- High transition frequency f<sub>T</sub>
- High gain of 8.2 dB and low noise of 1.8 dB at 3 V
- Optimum for RF amplification of a portable telephone and pager

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector to base voltage	$V_{CBO}$	9	V	
Collector to emitter voltage	V <sub>CEO</sub>	6	V	
Emitter to base voltage	$V_{EBO}$	1	V	
Collector current	$I_{C}$	30	mA	
Collector power dissipation	$P_{C}$	100	mW	
Junction temperature	T <sub>j</sub>	125	°C	
Storage temperature	$T_{stg}$	-55 to +125	°C	

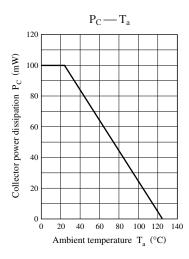


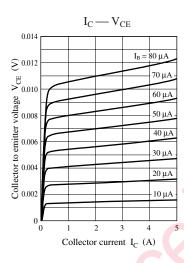
Marking symbol: 5A

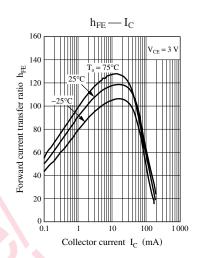
### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

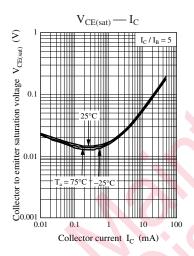
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector cutoff current	I <sub>CBO</sub>	$V_{CB} = 9 \text{ V}, I_{E} = 0$			1	μΑ
Emitter cutoff current	I <sub>EBO</sub>	$V_{EB} = 1 \text{ V}, I_C = 0$			1	μΑ
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}$	100		160	_
Forward transfer gain	S <sub>21e</sub>   <sup>2</sup>	$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}, f = 2 \text{ GHz}$	7.0	9.0		dB
Noise figure	NF	$V_{CE} = 3 \text{ V}, I_{C} = 3 \text{ mA}, f = 1.5 \text{ GHz}$		2.0	4.0	dB
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 3 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$		0.6	0.9	pF
Gain bandwidth product	$f_{\mathrm{T}}$	$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}, f = 2 \text{ GHz}$		12.5		GHz

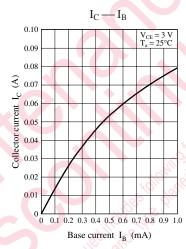
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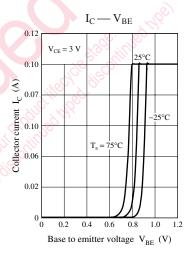


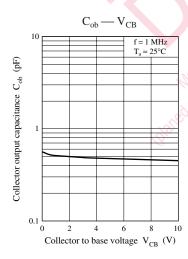












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